

# **One Watt Amplifier Transistors PNP Silicon**

# MPSW55 MPSW56\*

\*ON Semiconductor Preferred Device

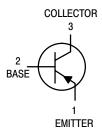
# **MAXIMUM RATINGS**

Rating	Symbol	MPSW55	MPSW56	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	-60	-80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-60	-80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-4.0		Vdc
Collector Current — Continuous	I <sub>C</sub>	-500		mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.0 8.0		Watt mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C



# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W



# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	MPSW55 MPSW56	V <sub>(BR)CEO</sub>	-60 -80		Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = -100 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	-4.0	_	Vdc
Collector Cutoff Current $(V_{CE} = -40 \text{ Vdc}, I_B = 0)$ $(V_{CE} = -60 \text{ Vdc}, I_B = 0)$	MPSW55 MPSW56	I <sub>CES</sub>	_	-0.5 -0.5	μAdc
Collector Cutoff Current $(V_{CB} = -40 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$	MPSW55 MPSW56	I <sub>CBO</sub>	_ _	-0.1 -0.1	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -3.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	_	-0.1	μAdc

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MPSW55 MPSW56

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS <sup>(1)</sup>				
DC Current Gain $ (I_C = -50 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) $ $ (I_C = -250 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) $	h <sub>FE</sub>	100 50		_
Collector–Emitter Saturation Voltage $(I_C = -250 \text{ mAdc}, I_B = -10 \text{ mAdc})$	V <sub>CE(sat)</sub>	_	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = –250 mAdc, V <sub>CE</sub> = –5.0 Vdc)	V <sub>BE(on)</sub>	_	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product (I <sub>C</sub> = -250 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 20 MHz)	f⊤	50	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>obo</sub>	_	15	pF

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

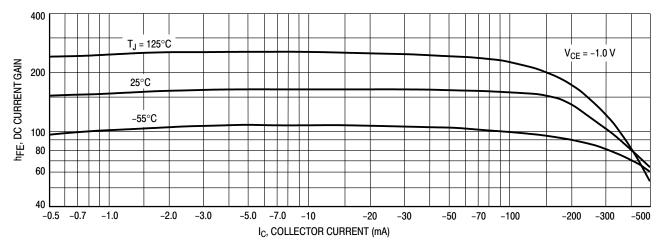


Figure 1. DC Current Gain

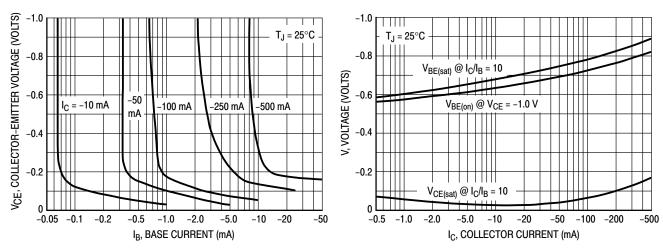
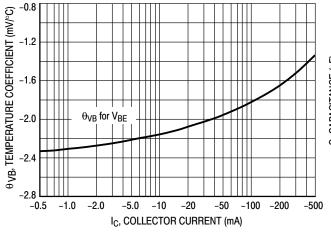


Figure 2. Collector Saturation Region

Figure 3. "On" Voltages

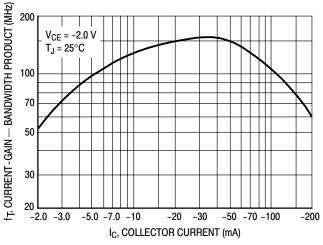
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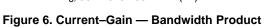


100 70 50 C, CAPACITANCE (pF) 30 20 10 7.0 5.0 -0.5 -1.0 -0.2 -2.0 -5.0 -10 -50 -100 -0.1 V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

Figure 4. Base-Emitter Temperature Coefficient

Figure 5. Capacitance





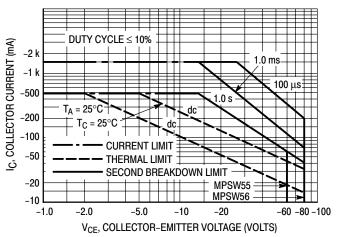
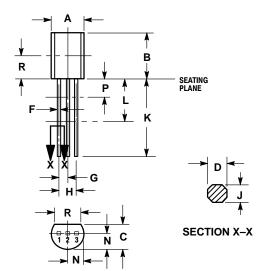


Figure 7. Active Region — Safe Operating Area

#### MPSW55 MPSW56

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-10 **ISSUE AL** 



PIN 1. EMITTER

BASE COLLECTOR

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L.
  DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.44	5.21	
В	0.290	0.310	7.37	7.87	
С	0.125	0.165	3.18	4.19	
D	0.018	0.021	0.457	0.533	
F	0.016	0.019	0.407	0.482	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.018	0.024	0.46	0.61	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.135		3.43		

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